編號: 127

國立成功大學 107 學年度碩士班招生考試試題

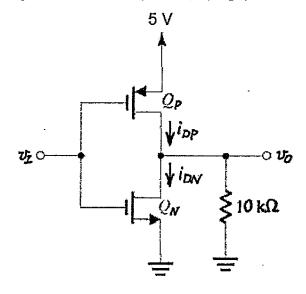
系 所:工程科學系 考試科目:電子電路

考試日期:0206,節次:1

第1頁,共3頁

※ 考生請注意:本試題可使用計算機。 請於答案卷(卡)作答,於本試題紙上作答者,不予計分。

- 1. Mark each of the following statements True (T) or False (F). (Need NOT give reasons.) (20 pt.)
 - (a) MOS is a symmetric device.
 - (b) BJT is also a symmetric device.
 - (c) For the CS circuit, when v_I increases from 0 to V_{DD} volt, the operation region of the MOS changes from cutoff, then triode, finally to saturation regions.
 - (d) Small-signal input is used to ensure that the BJT always operates in active mode.
 - (e) To guarantee the linear amplification of a MOSFET, we only have to design its DC operating point in the saturation region.
 - (f) The voltage drop of a current mirror can reduce the maximum output swing.
 - (g) The ideal current buffer has the properties: $R_{in} = \infty$, $R_{out} = 0$, and the current gain $A_i = 0$.
 - (h) The output resistance of a current mirror as an active load can reduce the voltage gain.
 - (i) For the IC amplifier design, it does not matter if the channel length modulation of MOS is neglected.
 - (j) The CG amplifier can be used for the current buffer, which ideally has $R_{\rm in} = 0$, $R_{\rm out} = \infty$, and the current gain $A_i = \infty$.
- 2. The NMOS and PMOS are matched with $k'_n \left(\frac{W}{L} \right)_n = k'_p \left(\frac{W}{L} \right)_p = 1 \text{ mA/V}^2$, $V_{tn} = -V_{tp} = 1 \text{ V}$, and $\lambda = 0$. Find i_{DN} , i_{DP} , and v_O for $v_I = 0 \text{ V}$ and 5 V, respectively. (20 pt.)



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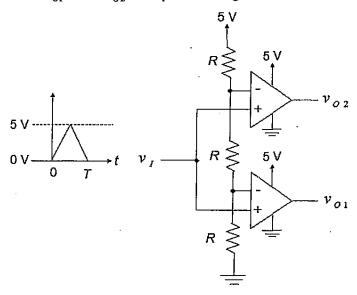
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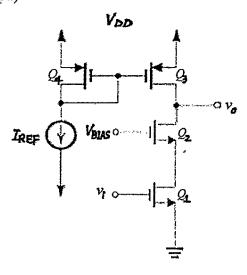
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第2頁,共3頁

3. The operational amplifiers are ideal. $R = 100 \text{ k}\Omega$. (a) Determine v_{01} and v_{02} when $v_I = 2.5 \text{ V}$. (b) Plot the output waveform of v_{01} and v_{02} if v_I is a triangular waveform as shown in the figure. (20 pt.)



4. For the following amplifier, $I_{REF} = 1 \text{ mA}$ and $V_{DD} = 10 \text{ V}$. For all transistors, $k'_n = k'_p = 500 \ \mu\text{A/V}^2$, $|V_{ln}| = |V_{lp}| = 1 \text{ V}$, $(W/L)_4 = 1 \ \mu\text{m}/\mu\text{m}$, $(W/L)_1 = (W/L)_2 = (W/L)_3 = 4 \ \mu\text{m}/\mu\text{m}$, and, for both NMOS and PMOS, $|V_A| = 100 \text{ V}$. (a) Analyze the voltage gain $A_v = \frac{v_o}{v_i}$. (b) Try to increase the magnitude of voltage gain by changing the active output load of the current mirror using the cascade transistor. What's the voltage gain you obtain? (20 pt.)



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5. Find R_o , R_{in3} , and $G_m = \frac{i_o}{v_i}\Big|_{v_o=0}$. Assume $r_{o1} = r_{o2} = r_{o3} = r_{o4} = r_{o5} = 100 \text{ k}\Omega$ and

$$g_{m1} = g_{m2} = g_{m3} = g_{m4} = g_{m5} = 10 \text{ mA/V.} (20 \text{ pt.})$$

